

AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph beginning at page 5, line 16, with the following rewritten paragraph:

-- The invention concerns a method for producing a transistor 1 for active matrix display comprising the steps of forming an active material 14 and electrodes 2, said active material being formed using vapor deposition methods and said transistor 1 comprising an insulator 3. The 20 vapor deposition methods use, for example, radiofrequency glow discharge technique. In a particular embodiment, one uses a 13.56 MHz PECVD reactor. However, said reactor can be powered by radiofrequency energy at another frequency. The vapor deposition methods can implement also a microwave ECR (electron 25 cyclotron resonance) technique.--